

METHOD AND APPARATUS FOR FABRICATING THIN FILM
TRANSISTOR INCLUDING CRYSTALLINE ACTIVE LAYER

5 ABSTRACT OF THE DISCLOSURE

10 The present invention relates to a method and apparatus for fabricating a thin
film transistor including a crystalline silicon active layer. According to the method of
the present invention, there are advantages in that processing time and production
costs can be reduced since a series of processes of fabricating the thin film transistor,
such as deposition of source metal, thermal annealing for crystallization, and
deposition of an insulating layer or a wiring metal layer, can be consecutively
performed in one apparatus.